



TO-252 (DPAK)

Pin Definition:

1. Gate 2. Drain

3. Source

Features

- Advanced Trench Technology
- Low R_{DS(ON)} 75mΩ (Max.)
- Low gate charge typical @ 20.9nC (Typ.)
- Low Crss typical @ 58pF (Typ.)

Ordering Information

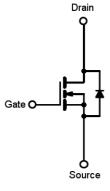
Part No.	Package	Packing
TSM15N15CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)
150	75 @ V _{GS} =10V	12

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	150	V	
Gate-Source Voltage		V _{GS}	±30	V	
Continuous Drain Current	T _C =25℃		12		
	T _C =70℃		9	А	
	T _A =25℃	– I _D	4		
	T _A =70℃		3	l	
Drain Current-Pulsed Note 1		I _{DM}	30	А	
Avalanche Current, L=0.1mH		I _{AS} , I _{AR}	8.2	А	
Avalanche Energy, L=0.1mH		E_{AS},E_{AR}	100	mJ	
Maximum Power Dissipation	T _C =25℃		15.6		
	T _C =70℃		10	W	
	T _A =25℃	– P _D	2		
	T _A =70℃		1.3		
Storage Temperature Range		T _{STG}	-55 to +150	ĉ	
Operating Junction Temperature Range		TJ	-55 to +150	c	

* Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	RƏ _{JC}	8	°C/W
Thermal Resistance - Junction to Ambient	RƏ _{JA}	62	°C/W



Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	•					1
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	150			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 10A$	R _{DS(ON)}		62	75	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \text{uA}$	V _{GS(TH)}	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 120V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic	·					
Total Gate Charge	V _{DS} = 75V, I _D = 10A, V _{GS} = 10V	Qg		20.9		nC
Gate-Source Charge		Q _{gs}		4.4		
Gate-Drain Charge		Q _{gd}		6.5		
Input Capacitance	V _{DS} = 30V, V _{GS} = 0V, f = 1.0MHz	C _{iss}		980		pF
Output Capacitance		C _{oss}		127		
Reverse Transfer Capacitance		C _{rss}		58		
Switching	·					
Turn-On Delay Time		t _{d(on)}		26		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 75V,$	t _r		14		
Turn-Off Delay Time	$R_{G} = 3\Omega$	t _{d(off)}		73		nS
Turn-Off Fall Time		t _f		18		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =10A	V _{SD}	-	0.8	1.3	V
Reverse Recovery Time	I _S = 10A, T _J =25 °C	t _{fr}		56		nS
Reverse Recovery Charge	dI/dt = 500A/us	Q _{fr}		151		nC

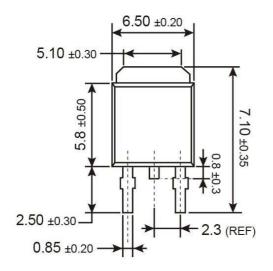
Notes:

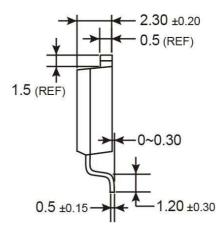
1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

2. $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air



TO-252 Mechanical Drawing





Unit: Millimeters



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